Amendments to the Specification:

Please amend the paragraph beginning on page ~~5~~ 4, line ~~9~~ 19, as follows:

As aforementioned, the present invention provides a package assembly for an electronic device. The package assembly comprises a substrate and a buffer layer. The substrate has a first surface with a first plurality of contact pads and a second plurality of contact pads, a second surface with a plurality of connection pads, and a plurality of via holes connecting the first plurality of contact pads and the plurality of connection pads. The buffer layer is between the substrate and the electronic device, and a surface of the electronic device has electrodes opposite to the first surface of the substrate. The buffer layer has an opening to expose the first plurality of contact pads. Wherein the buffer layer surrounds the edge of the electronic device and a fastening face of the edge of the electronic device and the buffer layer is unflattenedunflatened.

J.G. 4.19.07

Please amend the paragraph beginning on page ~~6~~ 5, line ~~1~~ 9 as follows:

layer surrounds the edge of the plurality of electronic devices, and fastening faces of the edge of the plurality of electronic devices and the buffer layer are unflattenedunflatened.

J.G. 4.19.07

Please amend the paragraph beginning on page ~~6~~ 5, line ~~5~~ 12 as follows:

The present invention further provides a packaging method for electronic devices. The method comprises: forming a buffer layer on a first surface of a substrate, the buffer layer having a first opening to expose a first plurality of contact pads on the first surface, wherein the substrate has the first surface with the first plurality of contact pads and a second plurality of contact pads, a second surface with a plurality of connection pads, and a plurality of via holes connecting the first plurality of contact pads and the plurality of connection pads; and mounting a first electronic device on the buffer layer corresponding to the first opening, wherein a surface of the electronic device having electrodes is opposite to the first surface of the substrate, the buffer layer surrounds the edge of the first electronic device,

and a fastening face of the edge of the first electronic devices and the buffer layer is unflattenedunflatened.

Please amend the paragraph beginning on page 8, line 23 as follows:

aims at these and provides a package assembly for electronic device with a buffer layer. The Flip-Chip ~~structre~~ structure and method of the present invention are very simple and the packaging hermeticity is also increased. In addition, the Flip-Chip technology is to flip the chip for connecting contact pads of the chip and contact pads of the substrate. The planarization (between the chip and the substrate) directly effects the yield of Flip-Chip, especially for gold-gold, and the request for planarization is more exact if the contact pads increases much more. Hence, the function of self-planarization during packaging can be achieved to reduce the problem of planarization through the buffer layer. The aforementioned advantages of the present invention will detailedly describe and illustrate as follows.

Please amend the paragraph beginning on page 9, line 2 as follows:

In general, if the gas were escaped from the space among the electronic device 10, the substrate 20, the buffer layer 30, and the second plurality of contact pads 40, fastening faces between the electronic device 10 and the buffer layer 30 and to pass through the buffer layer 30 are the main escaping way. In the present invention, the buffer layer 30 is pressed to intensify the density thereof and to extend along the space between the electronic device 10 and the substrate 20. Therefore, the thickness of the buffer layer becomes thicker and the fastening faces are not flat and have a corner due to pressure. Hence, compared with the conventional arts, the hermeticity in the present invention is very good. Moreover, a surface of the electronic device 10 fastening with the buffer layer 30 can not be flat, and may be ~~a unflatened~~ an unflattened surface, such as a sawtooth-shaped surface. Hence, the gas escaping distance is increased to raise the hermeticity.

Please amend the paragraph beginning on page 10, line 8 as follows:

bonding, a thermosonic bonding, soldering bonding, and an adhesive bonding, for tightly bonding the electronic device 10 with the buffer layer. In bonding process, a force 60 may be applied to the electronic device ~~60~~ 10 to intensify the solid of the portion of the buffer layer 30 connecting with the electronic device 10 for enhancing the resistance to erosions of moisture, oxygen, carbon dioxide, etc that can erode the electronic device or effect the reliability thereof. Furthermore, in the pressing process, the length of the buffer layer 30 is extended along the space between the electronic device 10 and the substrate 20 to extend the length of the gas escaping contour for increasing the escaping difficulty of gas passing through the buffer layer 30. Another gas escaping contour is the fastening face between the buffer layer 30 and the electronic device 10. The fastening face is ~~unflatened~~ unflattened and has a corner, and the length thereof is also extended due to the pressure. Hence, the gas is also hard to escape through the fastening face. Accordingly, the structure of the present invention is better than the structure of the conventional arts. On the side, the bonding process may be proceeded under a vacuum, a particular gas, or a mixed gas, e.g. inert gas (nitrogen, hydrogen, helium, etc.), the mixed inert gas. The particular gas or the mixed gas can not include some gases that can erode the electronic device or effect the reliability thereof, such as: moisture, oxygen, carbon dioxide, etc. Hence, the inner gas of the packaged device does not effect the packaged device.

Please amend the paragraph beginning on page 11, line 19 as follows:

Types of the electronic device 10 applied with the present invention will not be limited. For example, the package assembly and the method of the present invention can apply to RF components, sensors, EPROM, CCD, semiconductor lasers, LED, SAW and so on. Material types of the substrate 20 applied with the present invention are also various, e.g.: A1, high temperature co-fired ceramics (HTCC), low temperature co-fired ceramics (LTCC), etc. The conventional substrates, such as a silicon wafer, polymer substrate, a glass substrate, etc, are also suitable for the present invention.